## **Triacs**

# **Silicon Bidirectional Thyristors**

... designed for full-wave ac control applications primarily in industrial environments needing noise immunity.

- Guaranteed High Commutation Voltage dv/dt — 500 V/µs Min @ T<sub>C</sub> = 25°C
- High Blocking Voltage VDRM to 800 V
- Photo Glass Passivated Junction for Improved Power Cycling Capability and Reliability

# MAC321 Series

TRIACs 20 AMPERES RMS 200 thru 800 VOLTS





### MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage <sup>(1)</sup> (T <sub>J</sub> = -40 to +125°C, 1/2 Sine Wave 50 to 60 Hz, Open Gate)  MAC321-4  MAC321-6  MAC321-8  MAC321-10	VDRM	200 400 600 800	Volts
Peak Gate Voltage	V <sub>GM</sub>	10	Volts
On-State Current RMS (T <sub>C</sub> = +75°C Full Cycle Sine Wave 50 to 60 Hz)	IT(RMS)	20	Amp
Peak Surge Current (One Full Cycle, 60 Hz, T <sub>C</sub> = +75°C preceded and followed by Rated Current)	ITSM	150	Amp
Circuit Fusing Considerations (t = 8.3 ms)	l <sup>2</sup> t	93	A <sup>2</sup> s
Peak Gate Power (T <sub>C</sub> = +75°C, Pulse Width = 2.0 μs)	P <sub>GM</sub>	20	Watts
Average Gate Power (T <sub>C</sub> = +75°C, t = 8.3 ms)	P <sub>G(AV)</sub>	0.5	Watt
Peak Gate Current	I <sub>GM</sub>	2.0	Amp
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.8	°C/W

<sup>1.</sup> VDRM for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



#### **MAC321 Series**

### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current $(V_D = Rated\ V_{DRM},\ Gate\ Open)$ $T_J = 25^{\circ}C$ $T_J = +125^{\circ}C$	I <sub>DRM</sub>	_		10 2.0	μA mA
Peak On-State Voltage (Either Direction) (I <sub>TM</sub> = 28 A Peak; Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2.0%)	V <sub>TM</sub>	_	1.4	1.7	Volts
Gate Trigger Current (Continuous dc) (Main Terminal Voltage = 12 Vdc, R <sub>L</sub> = 100 Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)	I <sub>GT</sub>	_   _   _	  -  -	100 100 100	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L$ = 100 Ohms) MT2(+), $G(+)$ MT2(+), $G(-)$ MT2(-), $G(-)$ (Main Terminal Voltage = Rated $V_{DRM}$ , $R_L$ = 10 k $\Omega$ , $T_J$ = +125°C) MT2(+), $G(+)$ ; MT2(-), $G(-)$ ; MT2(+), $G(-)$	Vgт	   0.2	_ _ _ _	2.0 2.0 2.0	Volts
Holding Current (Either Direction) (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = 200 mA)	Ιн	_	_	100	mA
Turn-On Time $(V_D = Rated V_{DRM}, I_{TM} = 28 A, I_{GT} = 120 mA,$ Rise Time = 0.1 $\mu$ s, Pulse Width = 2.0 $\mu$ s)	<sup>t</sup> gt	_	1.5	_	μs
Critical Rate of Rise of Off-State Voltage ( $V_D$ = Rated $V_{DRM}$ , Exponential Voltage Rise, Gate Open) $T_J = 25^{\circ}C$ $T_J = +125^{\circ}C$	dv/dt(s)	500 200	_	_	V/µs

### **TYPICAL CHARACTERISTICS**

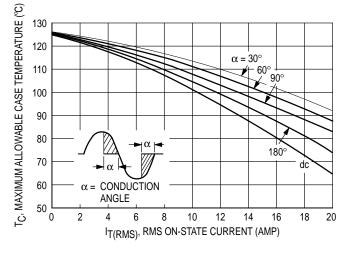


Figure 1. RMS Current Derating

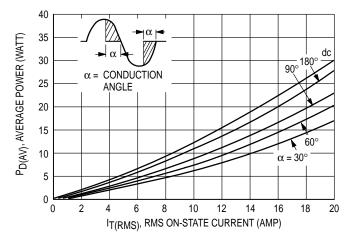


Figure 2. On-State Power Dissipation

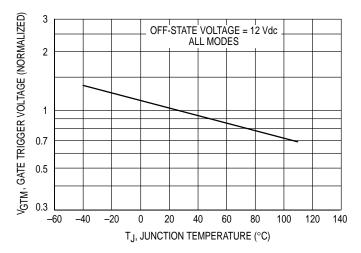


Figure 3. Typical Gate Trigger Voltage

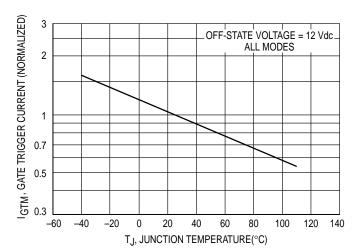


Figure 4. Typical Gate Trigger Current

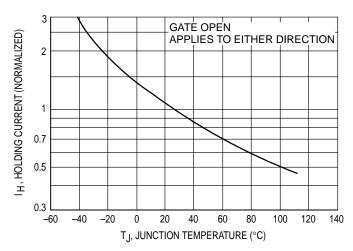


Figure 6. Typical Holding Current

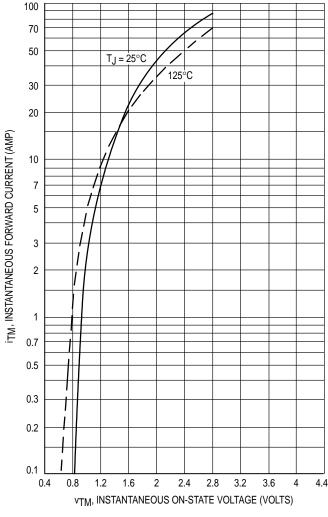


Figure 5. Maximum On-State Characteristics

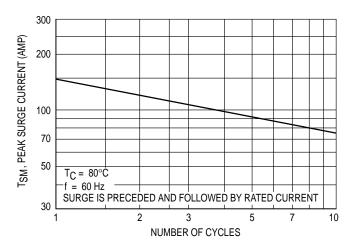


Figure 7. Maximum On-Repetitive Surge Current

### **MAC321 Series**

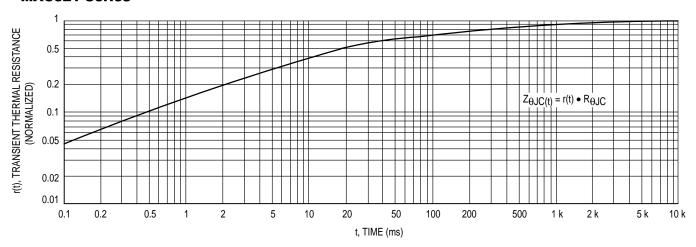
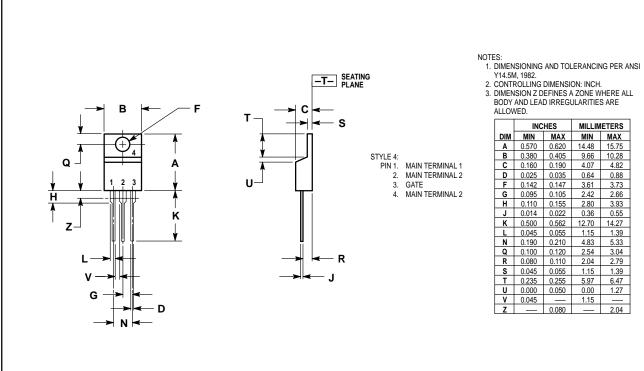


Figure 8. Thermal Response

### **PACKAGE DIMENSIONS**



	INCHES MILLIMETE		IETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.055	1.15	1.39
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

**CASE 221A-04** (TO-220AB)

#### **MAC321 Series**

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